



FORM 146 - SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		ATTORNEY DOCKET NO.: CIS-001CP
		APPLICANTS: Schowalter and Slack
		SERIAL NO.: 10/822,336
		FILING DATE: April 12, 2004
		GROUP: 1722

U.S. PATENT DOCUMENTS

EXAM INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
RK	A1	4,234,554	11/18/80	Rabenau et al.			
RK	A2	5,858,085	01/12/1999	Arai et al.			
RK	A3	5,858,086	01/12/1999	Hunter			
RK	A4	5,909,036	06/01/1999	Tanaka et al.			
RK	A5	5,972,109	10/26/1999	Hunter			
RK	A6	6,001,748	06/04/1997	Tanaka et al.			
RK	A7	6,045,612	04/04/2000	Hunter			
RK	A8	6,048,813	04/11/2000	Hunter			
RK	A9	6,063,185	05/16/2000	Hunter			
RK	A10	6,086,672	07/11/2000	Hunter			
RK	A11	6,187,089	02/13/2001	Phillips et al.			
RK	A11	6,296,956	10/02/2001	Hunter			

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
RK	B1	2000-154090	06/2000	JP				YES	N
RK	B2	02 018379A	01/22/1990	JP				YES	N
EXAMINER					DATE CONSIDERED				

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		ATTORNEY DOCKET NO.: CIS-001CP APPLICANTS: Schowalter and Slack SERIAL NO.: 10/822,336 FILING DATE: April 12, 2004 GROUP: 1722
OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
RK	C1	Dryburgh, "Estimation of maximum growth rate for aluminum nitride crystals by direct sublimation", <i>J. Crystal Growth</i> 125, 65-68 (1992).
RK	C2	A.S. Segal S. Yu, Karpov, Yu. N. Makarov, E.N. Mokhov, A.D. Roenkov, M.G. Ramm, Yu. A. Vodakov, "On mechanisms of sublimination growth of AlN bulk crystals", <i>J. Crystal Growth</i> 211, 68-72 (2000).
RK	C3	B. Raghorthamachar, W.M. Vetter, M. Dudley, R. Dalmau, R. Schlessner, Z. Sitar, E. Michaels, and J.W. Kolis, "Synchrotron white beam topography characterization of physical vapor transport grown AlN and ammonothermal GaN", <i>J. Crystal Growth</i> 246, 271-280 (2002).
RK	C4	R. Schlessner, R. Dalmau, and Z. Sitar, "Seeded growth of AlN bulk single crystals by sublimation", <i>J. Crystal Growth</i> 241, 416-420 (2002).
RK	C5	L.J. Schowalter, G.A. Slack, J.B. Whitlock, K. Morgan, S.B. Schujman, B. Raghorthamachar, M. Dudley, and K.R. Evans, "Fabrication of native, single-crystal AlN substrates", <i>Phys. Stat. Sol. (c)</i> , 104, (2003).
RK	C6	V. Noveski, R. Schlessner, S. Mahajan, S. Beaudoin, and Z. Sitar, "Growth of AlN crystals on AlN/SiC seeds by AlN powder sublimation in nitrogen atmosphere", <i>MRS Internet J. Nitride Semicond. Res.</i> 9, 2 (2004).
RK	C7	V. Noveski, R. Schlessner, S. Mahajan, S. Beaudoin, and Z. Sitar, "Mass transfer in AlN crystal growth at high temperatures", <i>J. Crystal Growth</i> 264, 369-378 (2004).
EXAMINER /Robert Kunemund/		DATE CONSIDERED 05/23/2006

LIBC/2667594.1

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)	1158.001CIP	Application Number
Applicant(s)	Schowalter et al	
Filing Date	Group Art Unit	

*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>	
RK	1.	G.A. Slack and T.F. McNelly, "Growth of High Purity AlN Crystals", J. Cryst. Growth 34, 263 (1976)
RK	2.	G.A. Slack and T.F. McNelly, "AlN Single Crystals", J. Cryst. Growth 42, 560 (1977)
RK	3.	B. Raghethamachar, M. Dudley, J.C. Rojo, K. Morgan, and L.J. Schowalter, "X-ray Characterization of Bulk AlN Single Crystals Grown by the Sublimation Technique", submitted to J. Crystal Growth (2002). Presented at Am. Assoc. Crystal Growth Conference. Seattle, WA, Aug. 2002.
RK	4.	S.V. Nagender Naidu and P. Rama Rao, Editors, "Phase Diagrams of Binary Tungsten Alloys, Indian Institute of Metals", Calcutta, pp. 7-13, (1991).
RK	5.	R. Dalmau, B. Raghethamachar, M. Dudley, R. Schlessler, and Z. Sitar, Materials Research Society Proc. Vol. 798, p. Y2.9.1 (2004).
RK	6.	B.M. Epelbaum, D. Hofmann, M. Bickermann, A. Winnacker, Mater. Sci. Forum 389-393, 1445 (2002).
RK	7.	G.A. Slack, J. Whitlock, K. Morgan, and L.J. Schowalter, Materials Research Society Proc. Vol. 798, p. Y10.74.1 (2004).
EXAMINER	/Robert Kunemund/	DATE CONSIDERED 05/23/2006

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.